

Form 1449*	Atty. Docket No.: 303.676US3	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Gurtej Singh Sandhu et al.	
	Filing Date: Herewith	Group: Unknown

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
472	3,900,312	08/19/1975	Terry, J.C., et al.	75	68 B	10/16/72
472	4,340,617	07/20/1982	Deutsch, et al.	427	53.1	05/19/80
472	4,343,870	08/10/1982	Heller, A., et al.	429	111	09/08/80
472	4,359,490	11/16/1982	Lehrer, W.I.	427	95	07/13/81
472	4,713,258	12/15/1987	Umemura	427	35	07/03/85
472	4,721,631	01/26/1988	Endo, et al.	427	66	03/09/87
472	4,751,101	06/14/1988	Joshi, R.V.	427	39	04/30/87
472	4,868,005	09/19/1989	Ehrlich, et al.	427	53.1	03/10/88
472	4,876,112	10/24/1989	Kaito, et al.	427	38	03/27/87
472	4,884,123	11/28/1989	Dixit, P., et al.	357	71	02/19/87
472	4,923,717	05/08/1990	Gladfelter, et al.	427	252	03/17/89
472	4,957,777	09/18/1990	Ilderem, V., et al.	427	55	10/12/89
472	4,971,655	11/20/1990	Stefano, et al.	156	659.1	12/26/89
472	5,005,519	04/01/1991	Egermeier, et al.	118	722	03/14/90
472	5,015,330	05/14/1991	Okumura, K., et al.	156	643	02/28/90
472	5,022,905	06/11/1991	Grundy, et al.	65	60.51	10/12/89
472	5,032,233	07/16/1991	Yu, C., et al.	204	192.28	09/05/90
472	5,049,975	09/17/1991	Ajika, N., et al.	357	71	03/12/90
472	5,124,780	06/23/1992	Sandhu, G.S., et al.	357	67	06/10/91
472	5,136,362	08/04/1992	Grief, et al.	357	67	11/27/90
472	5,147,819	09/15/1992	Yu, C., et al.	437	173	02/21/91
472	5,173,327	12/22/1992	Sandhu, G.S., et al.	427	573	06/18/91
472	5,192,589	03/09/1993	Sandhu, G.S.	427	255.1	09/05/91
472	5,196,360	03/23/1993	Doan, T.T., et al.	437	41	04/06/92
472	5,202,579	04/13/1993	Fujii, H., et al.	257	751	01/21/92
472	5,227,331	07/13/1993	Westmoreland, D.	437	174	02/10/92
472	5,227,334	07/13/1993	Sandhu	437	190	10/31/91
472	5,232,873	08/03/1993	Geva, M., et al.	437	192	10/13/92
472	5,240,739	08/31/1993	Doan, T., et al.	427	126.1	08/07/92
472	5,246,881	09/21/1993	Sandhu, G.S., et al.	437	192	04/14/93
472	5,252,518	10/12/1993	Sandhu, et al.	437	200	03/03/92
472	5,254,499	10/19/1993	Sandhu, G., et al.	437	192	07/14/92
472	5,258,096	11/02/1993	Sandhu, et al.	156	643	08/20/92
472	5,273,783	12/28/1993	Wanner	427	250	03/24/93
472	5,275,715	01/04/1994	Tuttle	205	123	01/23/92
472	5,278,100	01/11/1994	Doan, T.T., et al.	437	200	11/08/91
472	5,306,951	04/26/1994	Lee, et al.	257	755	05/14/92
472	5,320,880	06/14/1994	Sandhu, G.S., et al.	427	578	11/18/93
472	5,341,016	08/23/1994	Prall, K.D., et al.	257	412	06/16/93
472	5,344,792	09/06/1994	Sandhu, G.S., et al.	437	200	03/04/93
472	5,374,591	12/20/1994	Hasegawa, T., et al.	437	187	03/23/92

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JS	5,376,405	12/27/1994	Doan, T., et al.	427	126.1	04/15/93
JS	5,381,302	01/10/1995	Sandhu, G., et al.	361	305	08/10/93
JS	5,384,284	01/24/1995	Doan, T.T., et al.	437	190	10/01/93
JS	5,384,289	01/24/1995	Westmoreland, D.L.	437	245	06/17/93
JS	5,391,410	02/21/1995	Nii, T., et al.	427	578	05/28/93
JS	5,393,564	02/28/1995	Westmoreland, et al.	427	248.1	05/02/94
JS	5,399,379	03/21/1995	Sandhu	427	255.2	05/11/94
JS	5,416,045	05/16/1995	Kauffman, et al.	437	174	02/18/93
JS	5,425,392	06/20/1995	Thakur, et al.	437	173	05/26/93
JS	5,453,640	09/26/1995	Kinoshita, Y.	257	520	12/20/94
JS	5,459,353	10/17/1995	Kanazawa, M.	257	751	01/05/95
JS	5,496,762	03/05/1996	Sandhu, et al.	437	60	06/02/94
JS	5,506,166	04/09/1996	Sandhu, G.S., et al.	437	60	09/27/94
JS	5,508,066	04/16/1996	Akahori, T.	427	571	09/14/94
JS	5,567,243	10/22/1996	Foster, R.F., et al.	118	730	06/06/95
JS	5,571,572	11/05/1996	Sandhu, G.	427	585	06/30/94
JS	5,575,708	11/19/1996	Chau, S., et al.	451	305	07/07/95
JS	5,595,784	01/21/1997	Kaim, R., et al.	427	255.2	08/18/95
JS	5,607,722	03/04/1997	Vaartstra, et al.	427	248.1	02/09/96
JS	5,633,200	05/27/1997	Hu, Y.	438	653	05/24/96
JS	5,641,545	06/24/1997	Sandhu, G.S.	427	573	06/07/95
JS	5,644,166	07/01/1997	Honeycutt, J., et al.	257	754	07/17/95
JS	5,693,557	12/02/1997	Hirao, S., et al.	437	60	01/24/96
JS	5,747,116	05/05/1998	Sharan, S., et al.	427	534	01/16/96
JS	5,773,890	06/30/1998	Uchiyama, T., et al.	257	753	08/27/96
JS	5,828,131	10/27/1998	Cabral, Jr., C., et al.	257	757	01/16/96
JS	5,834,371	11/10/1998	Ameen, M.S., et al.	438	656	01/31/97
JS	5,838,052	11/17/1998	McTeer, A.	257	437	03/07/96
JS	5,956,595	09/21/1999	Zenke, M.	438	398	07/15/97
JS	5,973,402	10/26/1999	Shinriki, H., et al.	257	768	01/30/97
JS	5,976,976	11/02/1999	Doan, T.T., et al.	438	683	08/21/97
JS	6,031,288	02/29/2000	Todorobaru, H., et al.	257	754	11/12/96
JS	6,120,844	09/19/2000	Chen, L., et al.	427	255.28	03/27/96
JS	6,143,362	11/07/2000	Sandhu, G.S., et al.	427	255.391	02/25/98

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
JS	0798777	10/01/1997	European	H01L	21/768		
JS	8-176823	07/09/1996	Japan	C23C	16/02		
JS	98/34445	08/06/1998	PCT	H05K	3/26		

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No						

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	Bachmann, P., et al., "Plasma-Assisted Chemical Vapor Deposition Processes", <u>MRS Bulletin</u> , 52-59, (December 1988)
	Bouteville, A., et al., "TiSi2 Selective Growth in a rapid thermal low pressure chemical vapor depositoin system", <u>Journal of the Electrochemical Society</u> , 139, 2260-2263, (August 1992)
	Cowher, M., et al., "Low Temperature CVD Garnet Growth", <u>Journal of Crystal Growth</u> , 46, 399-402, (1979)
	Engqvist, J., et al., "Selective deposition of TiSi2 from H2-TiCl4 Gas mixtures and si: Aspects of Thermodynamics including Critical evaluation of thermochemical data in the Ti-Si System", <u>Journal of the Electrochemical Society</u> , 139, 3197-3205, (November 1992)
	Esquivel, A., et al., "Electrical and Physical Characteristics of Dry Oxygen, High Pressure Oxidation for SUB-0.5 um CMOS Isolation", <u>Abst. Int'l Electron Devices Meeting</u> , (1994)
	Herman, I., "Laser-Assisted Deposition of Thin Films from Gas-Phase and Surface-Adsorbed Molecules", <u>Chem. Rev.</u> , 89, 1323, 1346-1349, (1989)
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	Lie, L., et al., "High Pressure Oxidation of Silicon in Dry Oxygen", <u>J. Electrochemical Soc. : Solid State Science and Technology</u> , 129, 2828-2834, (Dec. 1982)
	Moeller, T., et al., "Semiconducting Elements, Ch. 30", <u>In: Chemistry with Inorganic Qualitative Analysis</u> , 2nd Edition, Academic Press, 995-996, (1984)
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Examiner <u>J. M. ONDT</u>	Date Considered <u>05/24/02</u>
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

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	Rosler, R., et al., "Plasma-Enhanced CVD of Titanium Silicide", <u>J. Vacuum Science Tech.</u> , B2(4), 733-737, (October/December 198)
	Wolf, S., <u>Silicon Processing for the VLSI Era, Vol. 2: Process Integration</u> , Lattice Press, Sunset Beach, California, 202-203, (1990)
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